

IN THE SPECIFICATION

Please replace the paragraph beginning at page 263, line 1, with the following rewritten paragraph:

ABSTRACT OF THE DISCLOSURE

A magnetoresistance effect element includes a nonmagnetic spacer layer, first and second ferromagnetic layer separated by the nonmagnetic spacer layer, and a nonmagnetic conductivity layer. The first ferromagnetic layer has a magnetization direction at an angle relative to a magnetization direction of the second ferromagnetic layer at zero applied magnetic field. The second ferromagnetic layer has first and second ferromagnetic films antiferromagnetically coupled to one another and an antiferromagnetically coupling film located between and in contact with the first and second ferromagnetic films. The magnetization of the first ferromagnetic layer freely rotates in a magnetic field signal. The nonmagnetic conductivity layer is disposed in contact with the first ferromagnetic layer so that the first ferromagnetic layer is disposed between the nonmagnetic high-conductivity layer and the nonmagnetic spacer layer. The first ferromagnetic layer has a film thickness between 0.5 nanometers and 4.5 nanometers.